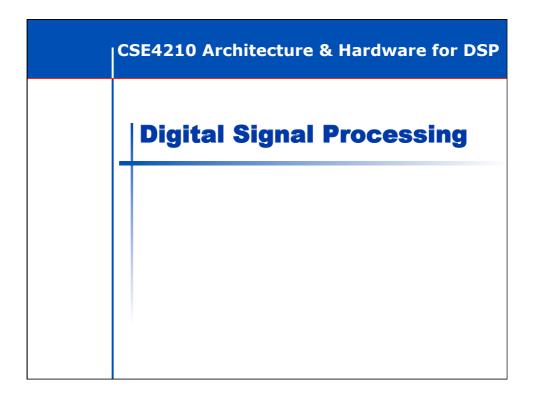
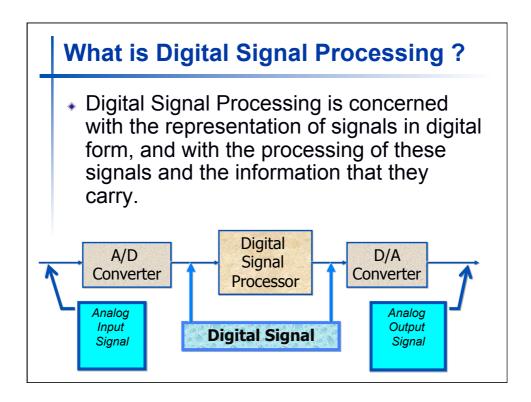
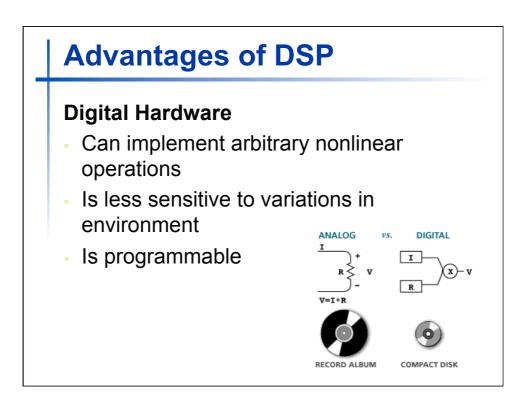


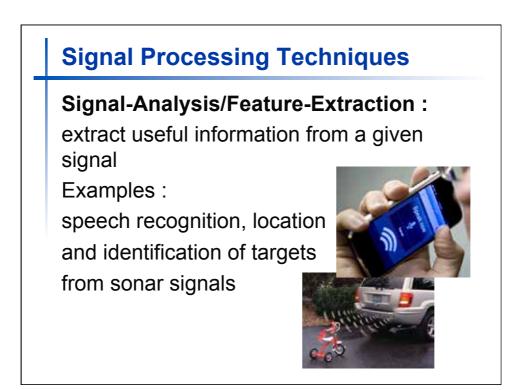


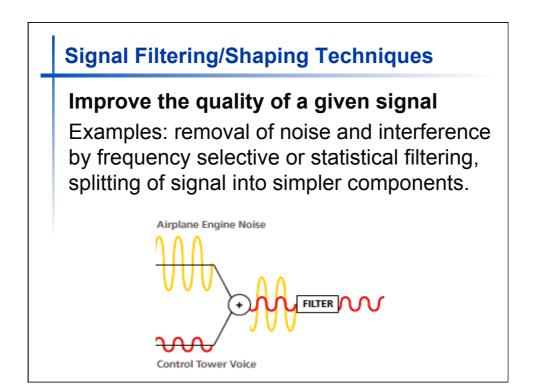
- Number systems
- Building blocks
- Algorithm representation
- Transformation (retiming, unfolding, folding)
- Mapping algorithms into hardware
- Low power design



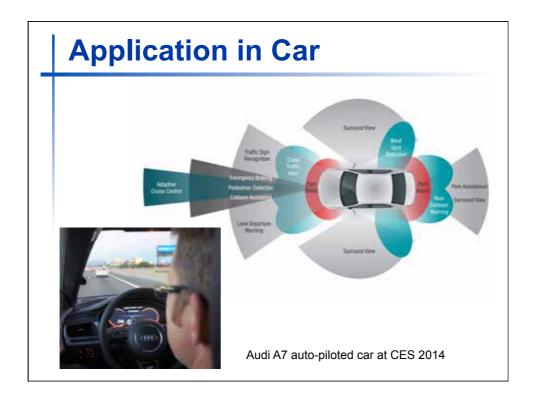


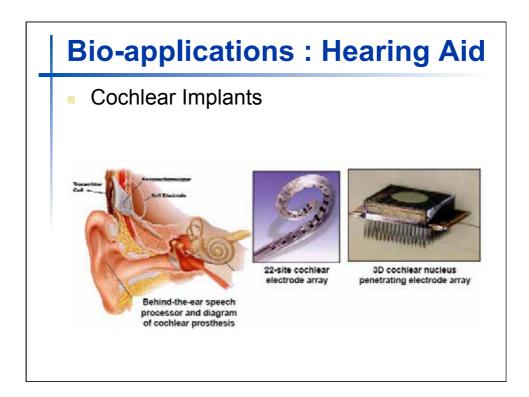


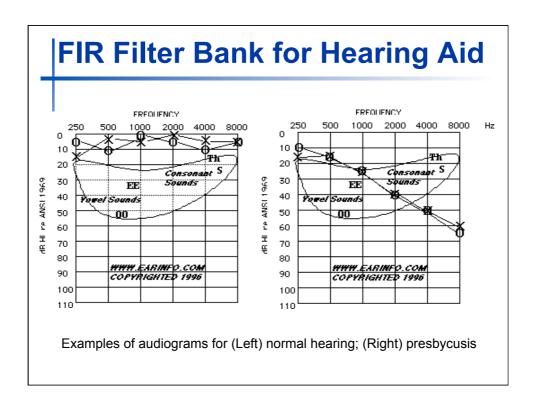


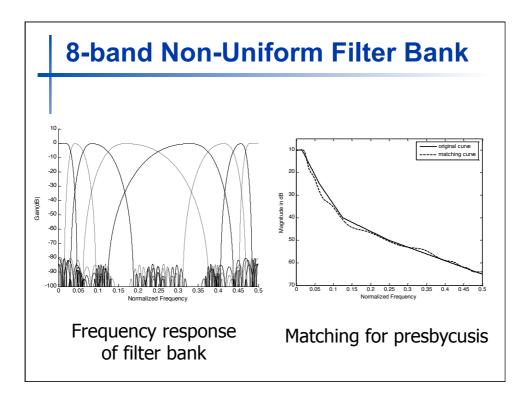


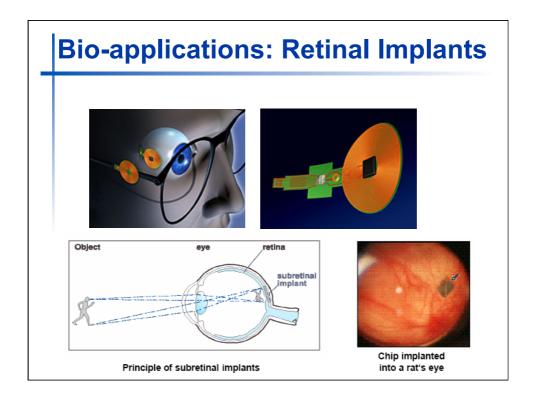


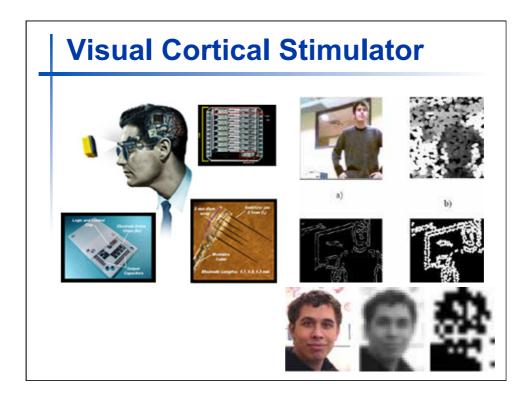


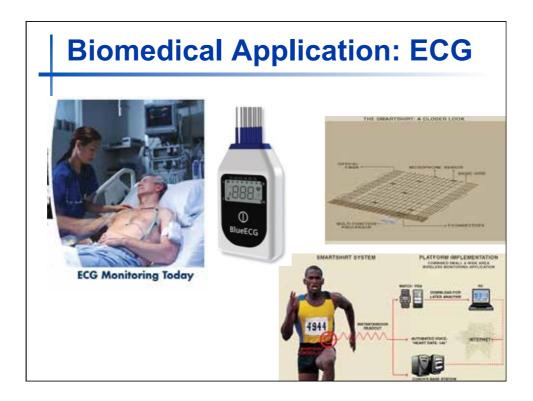


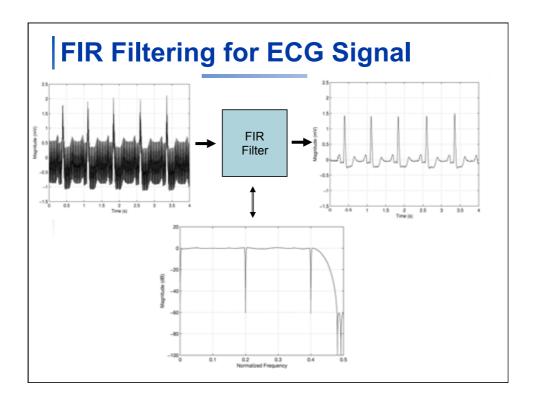


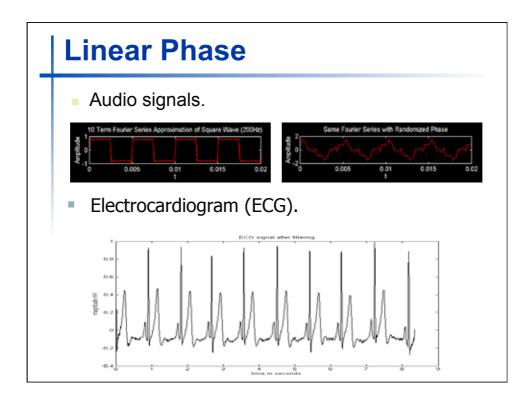




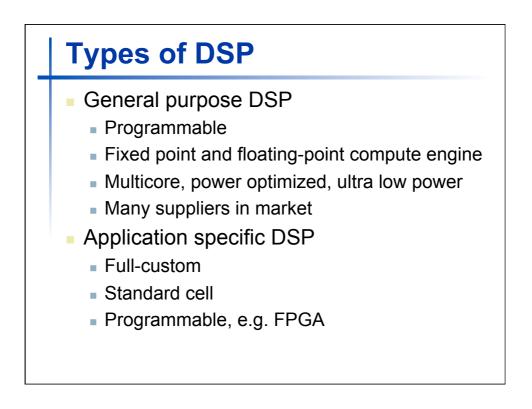








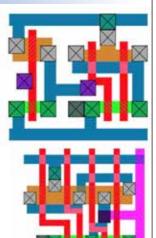


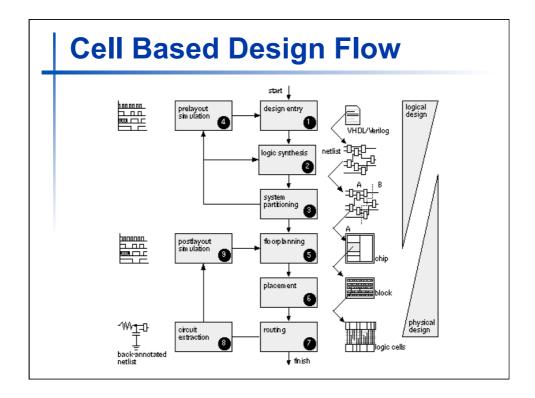


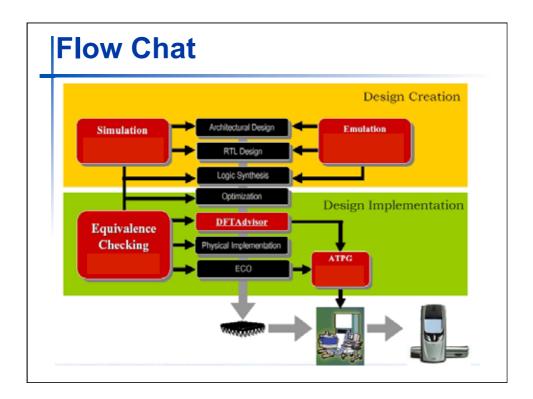
## Full Custom vs. Standard Cell

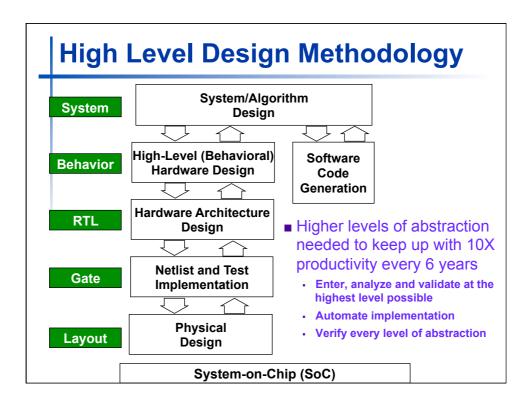
Full custom

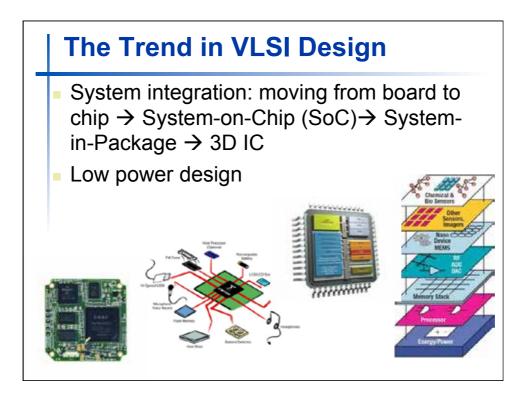
- Analog/digital with all customized mask layers and some logic cells
- Full control over sizing and layout
- Standard cell
  - Using pre-designed "cells"
  - Constant-height and regular pin locations

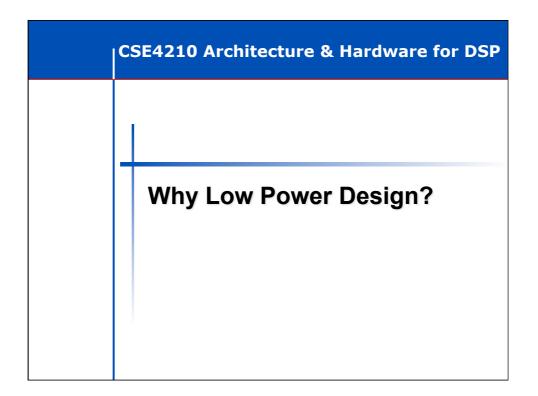




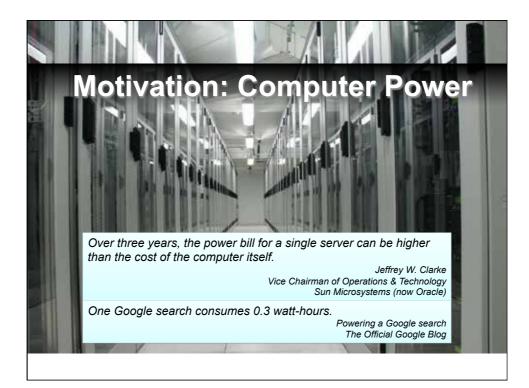


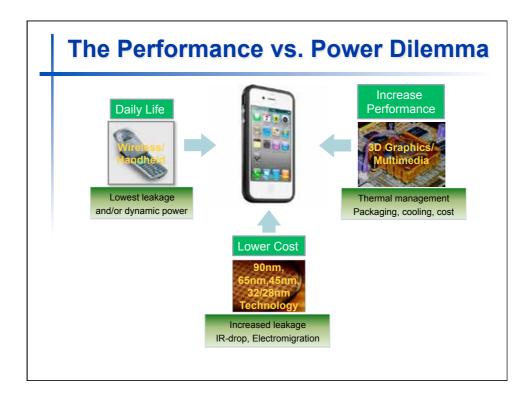


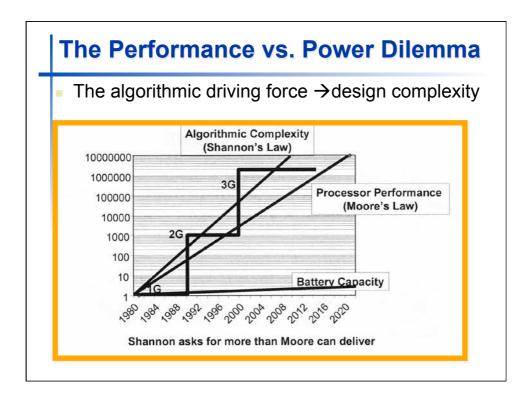


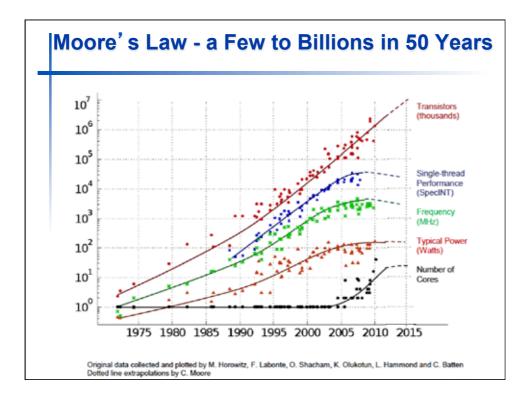






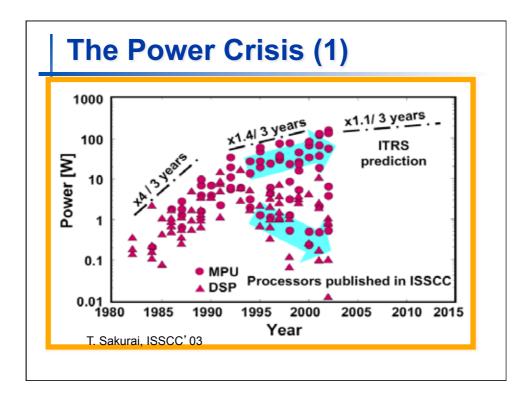


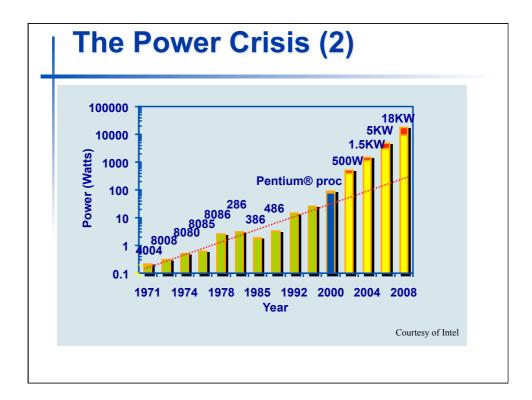


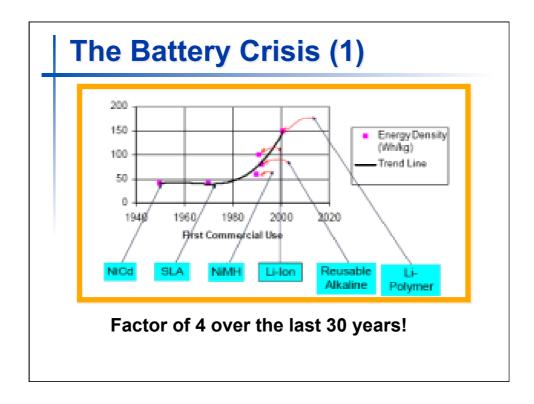


## Increasing Performance

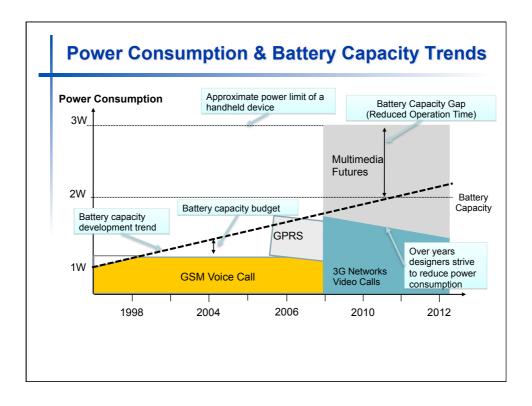
YEAR OF PRODUCTION	2003	20	006	2009	2010	2011	2015
Process Technology (nm)	130	ç	90	65	45	32/28	12
Supply Voltage (V)	1.2		1	0.8	0.6	0.5	0.3
Clock Frequency (MHz)	1000	20	000	2500	2900	3200	4000
Application (maximum required performance) Application (other)	Still Image Processing Web Browser	Real Time Video Codec (MPEG4/CIF)			Real Time Interpretation		
	Electric Mailer Scheduler	Voice R	elephone (1: ecognition (Ir ation(Crypto E	iput)	TV Telepho Voice Re (Oper	cognition	
Processing Performance (GOPS)	0.3	2	14		77	461	2458
Required Average Power (W)	0.1	0.1	0.1	0.1	0.1	0.1	0.1
Required Standby Power (mW)	2	2	2		2	2	2
Battery Capacity (Wh/Kg)	120	200	200		400	400	400

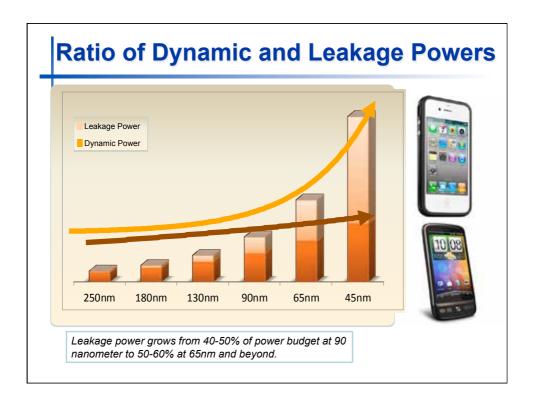


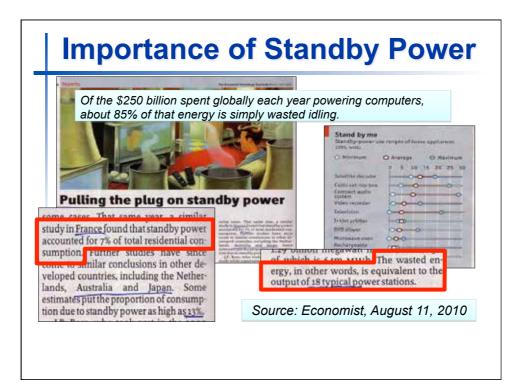


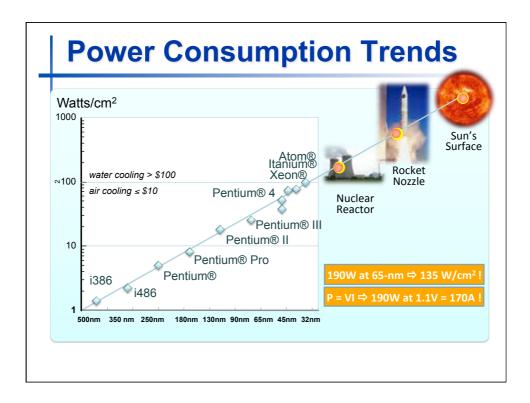


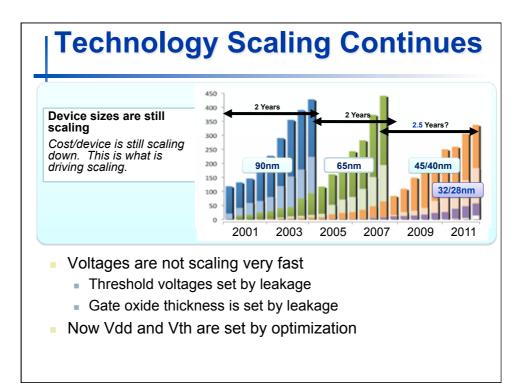
<ul> <li>store energy using a chemical reaction</li> <li>Battery capacity doubles every 10</li> <li>Gasoline 14</li> <li>Lead-Acid 0.04</li> </ul>	asic technology	Energy density of material	KWH/kg
	0, 0	Gasoline	14
	• • •	Lead-Acid	0.04
years Li polymer 0.15	-	Li polymer	0.15

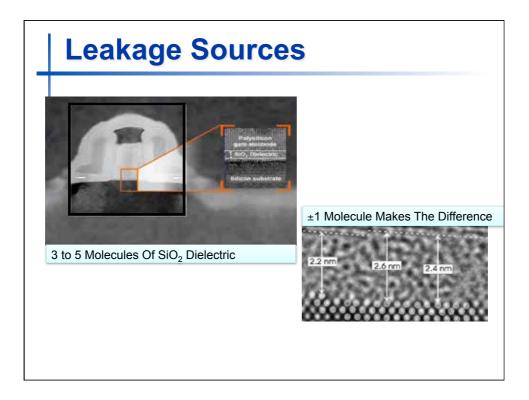


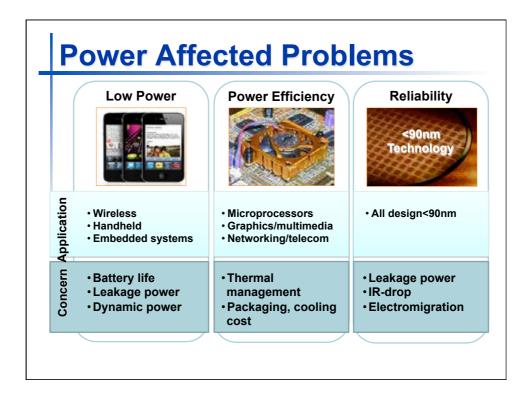












he Signs of							
Voltage Is Breaking the Rules of Scaling							
Source: ITRS 2005	90nm	65nm	45nm	32/28nm			
Device Length (nm) ⊃	1x	0.7x	0.5x	0.3x			
Delay (ps) ⊃	1x	0.7x	0.5x	03x			
Frequency (GHz) ⇒	1x	1.43x	2x	3x			
Integration Capacity (BT) ⇒	1x	2x	4x	8x			
Capacitance (fF) ⊃	1x	0.7x	0.5x	0.3x			
Die Size (mm²) 🗯	1x	1x	1x	1x			
Voltage (V) ►>	1x	0.85x	0.7x	0.55x			
Power <sub>Dyn</sub> (W) ►	1x	>0.7x	>0.5x	>0.3x			
Manufacturing (microcents/T) ⊃	1x	0.35x	0.12x	0.08x			
V <sub>TH</sub> (V) ►	1x	.85x	.7x	.55x			
I <sub>OFF</sub> (nA/um) ⇔⇔	1x	~3x	~9x	~22x			
Power <sub>Dyn</sub> Density (W/cm²) ⇒	1x	1.43x	2x	4x			
Power <sub>Leak</sub> Density (W/cm <sup>2</sup> ) ⇒	1x	~2.5x	~6.5x	~13.5x			
Power Density (W/cm <sup>2</sup> ) ⇒	1x	~2x	~4x	~8x			
Cu Resistance (Ω) ⇒	1x	2x	4x	8x			
Interconnect RC Delay (ps) ⇒	1x	~2x	~5x	~12x			
Packaging (cents/pin) ►>	1x	0.86x	0.73x	0.58x			
Test (nanocents/T) 单	1x	1x	1x	1x			

